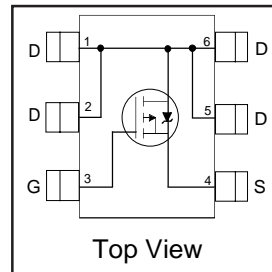


IRLMS6802

HEXFET® Power MOSFET

- Ultra Low On-Resistance
- P-Channel MOSFET
- Surface Mount
- Available in Tape & Reel

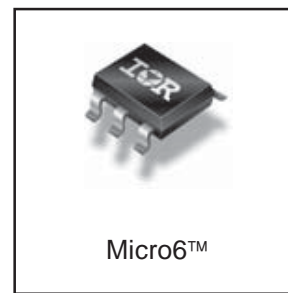


$V_{DSS} = -20V$
$R_{DS(on)} = 0.050\Omega$

Description

These P-Channel MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit provides the designer with an extremely efficient device for use in battery and load management applications.

The Micro6™ package with its customized leadframe produces a HEXFET® power MOSFET with $R_{DS(on)}$ 60% less than a similar size SOT-23. This package is ideal for applications where printed circuit board space is at a premium. The unique thermal design and $R_{DS(on)}$ reduction enables a current-handling increase of nearly 300% compared to the SOT-23.



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain- Source Voltage	-20	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V$	-5.6	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V$	-4.5	
I_{DM}	Pulsed Drain Current ①	-45	
$P_D @ T_A = 25^\circ C$	Power Dissipation	2.0	W
$P_D @ T_A = 70^\circ C$	Power Dissipation	1.3	
	Linear Derating Factor	0.016	W/°C
E_{AS}	Single Pulse Avalanche Energy②	31	mJ
V_{GS}	Gate-to-Source Voltage	± 12	V
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 150	°C

Thermal Resistance

	Parameter	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient③	62.5	°C/W

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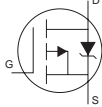
1

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Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	-20	—	—	V	V _{GS} = 0V, I _D = -250μA
ΔV _{(BR)DSS/ΔT_J}	Breakdown Voltage Temp. Coefficient	—	-0.005	—	V/°C	Reference to 25°C, I _D = -1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	—	0.050	Ω	V _{GS} = -4.5V, I _D = -5.1A ②
		—	—	0.100		V _{GS} = -2.5V, I _D = -3.4A ②
V _{GS(th)}	Gate Threshold Voltage	-0.60	—	-1.2	V	V _{DS} = V _{GS} , I _D = -250μA
g _{fs}	Forward Transconductance	1.5	—	—	S	V _{DS} = -10V, I _D = -0.80A
I _{DSS}	Drain-to-Source Leakage Current	—	—	-1.0	μA	V _{DS} = -16V, V _{GS} = 0V
		—	—	-25		V _{DS} = -16V, V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	-100	nA	V _{GS} = -12V
	Gate-to-Source Reverse Leakage	—	—	100		V _{GS} = 12V
Q _g	Total Gate Charge	—	11	16	nC	I _D = -4.5A
Q _{gs}	Gate-to-Source Charge	—	2.2	3.3		V _{DS} = -10V
Q _{gd}	Gate-to-Drain ("Miller") Charge	—	2.9	4.3		V _{GS} = -5.0V ②
t _{d(on)}	Turn-On Delay Time	—	12	—	ns	V _{DD} = -10V
t _r	Rise Time	—	33	—		I _D = -1.0A
t _{d(off)}	Turn-Off Delay Time	—	70	—		R _G = 6.0Ω
t _f	Fall Time	—	72	—		R _D = 10Ω ②
C _{iss}	Input Capacitance	—	1079	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	220	—		V _{DS} = -10V
C _{rss}	Reverse Transfer Capacitance	—	152	—		f = 1.0MHz

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	-2.0	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I _{SM}	Pulsed Source Current (Body Diode) ①	—	—	-45		
V _{SD}	Diode Forward Voltage	—	—	-1.2	V	T _J = 25°C, I _S = -1.6A, V _{GS} = 0V ③
t _{rr}	Reverse Recovery Time	—	74	110	ns	T _J = 25°C, I _F = -3.0A
Q _{rr}	Reverse Recovery Charge	—	45	67	nC	di/dt = -100A/μs ②

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② Pulse width ≤ 400μs; duty cycle ≤ 2%.
- ③ Surface mounted on FR-4 board, t ≤ 5sec.
- ④ Starting T_J = 25°C, L = 6.8mH
R_G = 25Ω, I_{AS} = -3.0A. (See Figure 12)

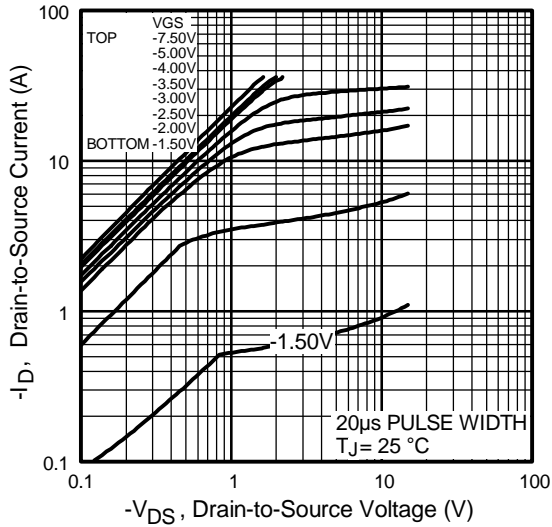


Fig 1. Typical Output Characteristics

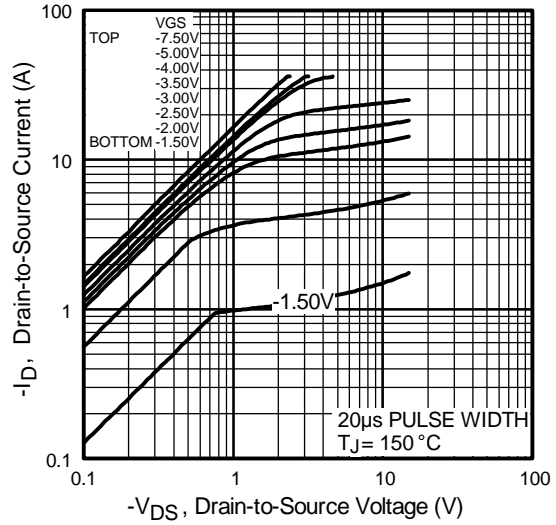


Fig 2. Typical Output Characteristics

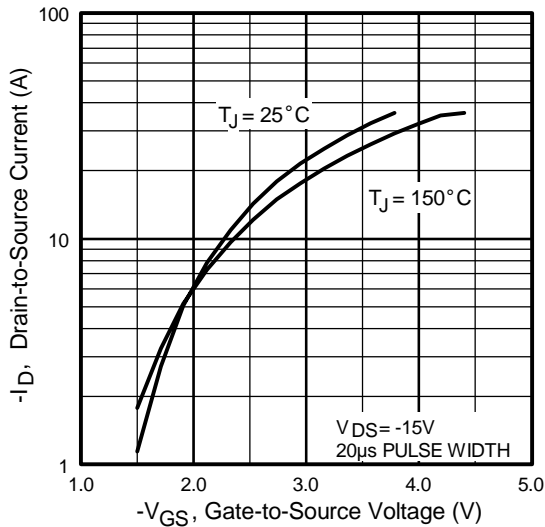


Fig 3. Typical Transfer Characteristics

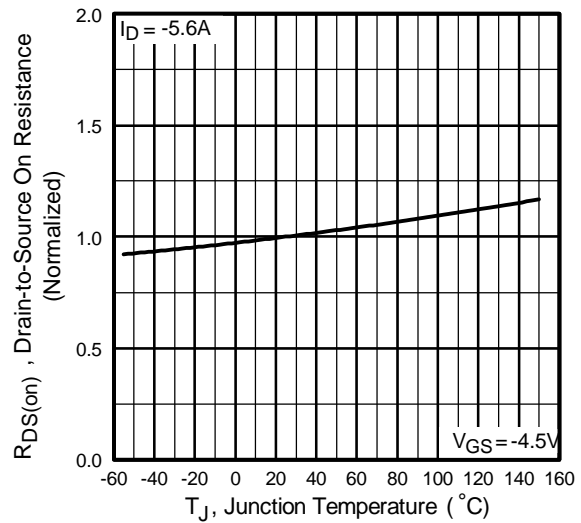


Fig 4. Normalized On-Resistance Vs. Temperature

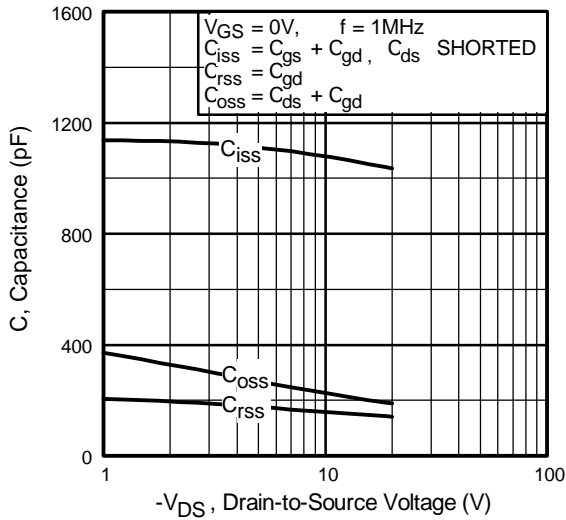


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

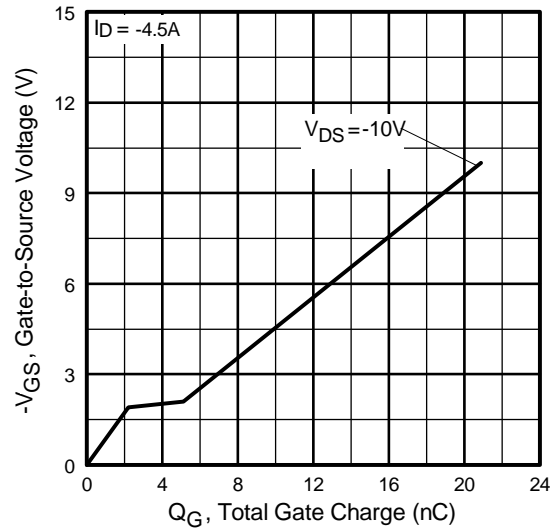


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

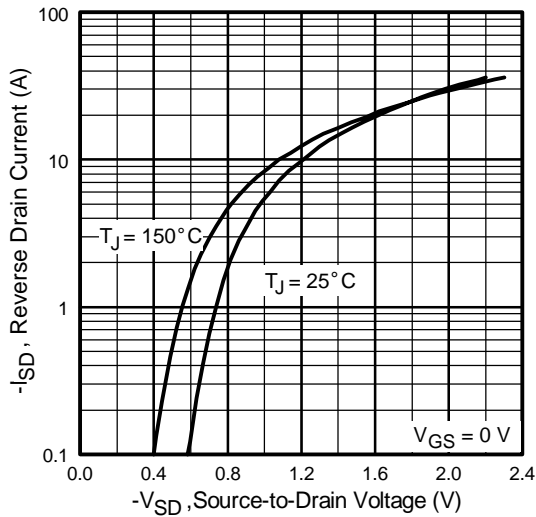


Fig 7. Typical Source-Drain Diode Forward Voltage

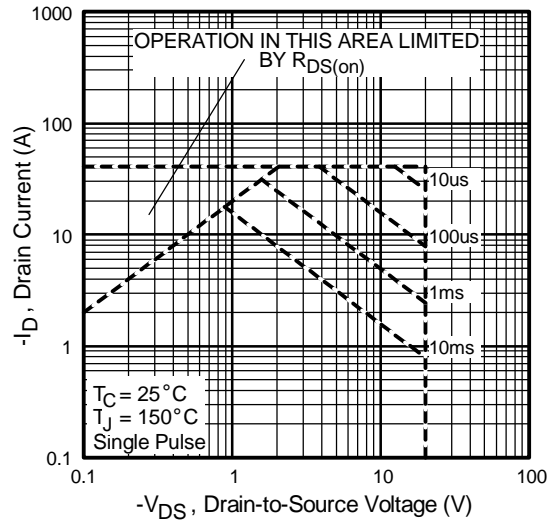


Fig 8. Maximum Safe Operating Area

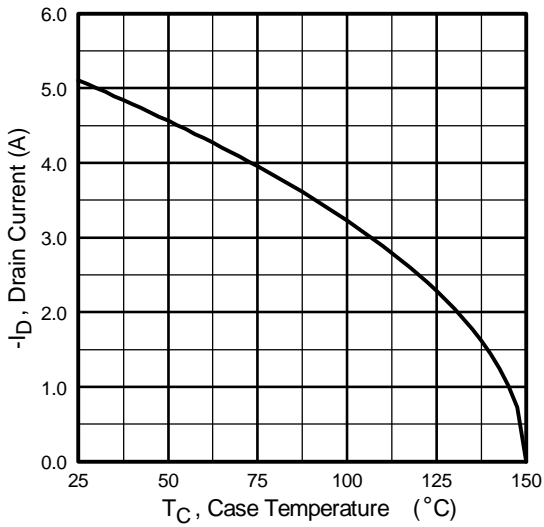


Fig 9. Maximum Drain Current Vs. Case Temperature

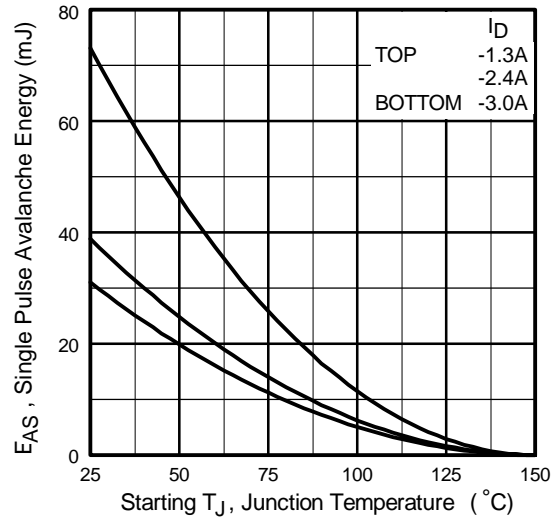


Fig 10. Maximum Avalanche Energy Vs. Drain Current

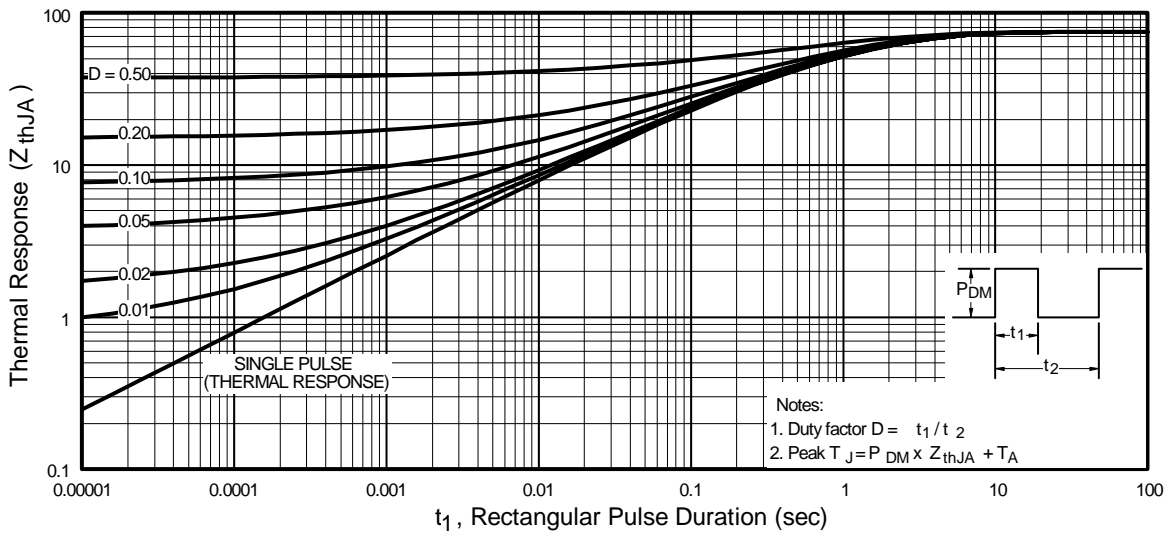
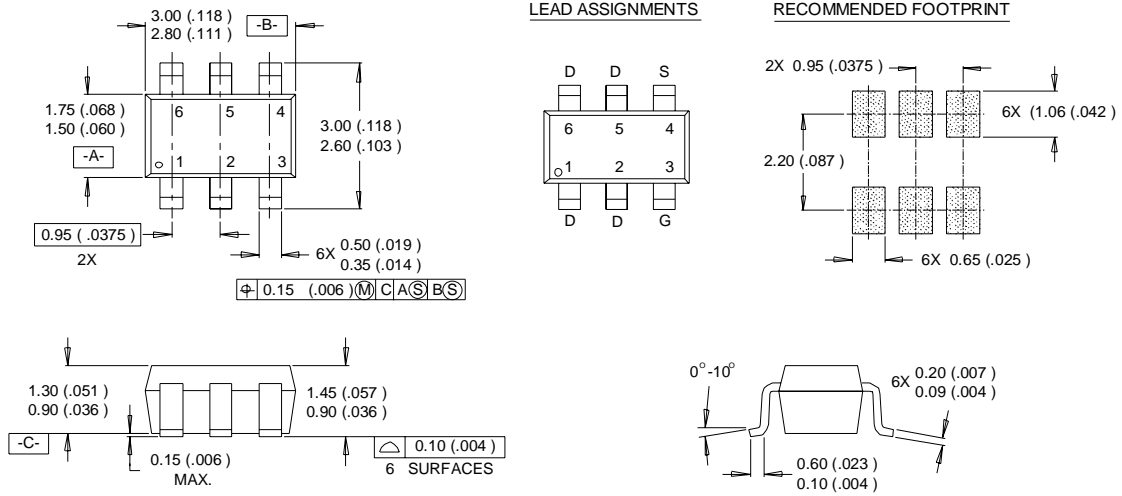


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

IRLMS6802

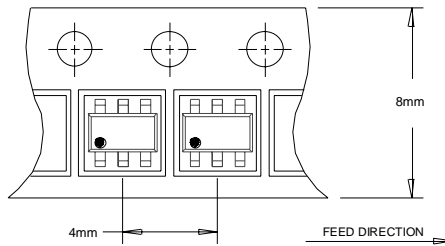
International
IR Rectifier

Micro6™ Package Outline

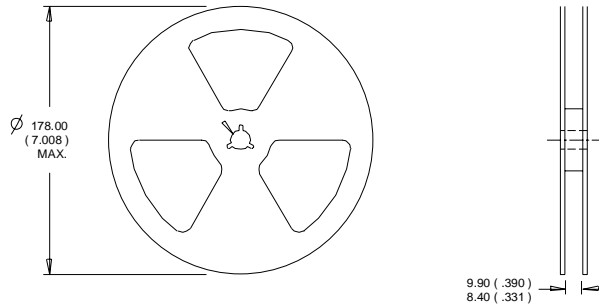


- NOTES :
1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1982.
 2. CONTROLLING DIMENSION : MILLIMETER.
 3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).

Micro6™ Tape & Reel Information



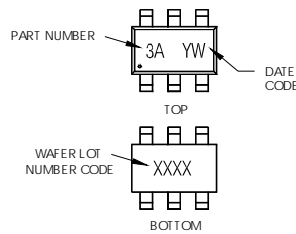
- NOTES :
1. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
 2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Micro6™ Part Marking Information

Notes: This part marking information applies to devices produced before 02/26/2001
 EXAMPLE: THIS IS AN IRLMS6702 WW = (1-26) IF PRECEDED BY LAST DIGIT OF CALENDAR YEAR



PART NUMBER CODE REFERENCE:

- 2A = IRLMS1902
- 2B = IRLMS1503
- 2C = IRLMS6702
- 2D = IRLMS5703
- 2E = IRLMS6802
- 2F = IRLMS4502
- 2G = IRLMS2002
- 2H = IRLMS6803

DATE CODE EXAMPLES:

- YW = 9603 = 6C
- YW = 9632 = FF

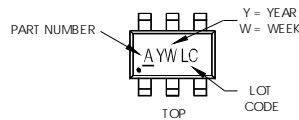
YEAR	Y	WORK WEEK	W
2001	1	01	A
2002	2	02	B
2003	3	03	C
2004	4	04	D
2005	5		
1996	6		
1997	7		
1998	8		
1999	9		
2000	0	24	X
		25	Y
		26	Z

WW = (27-52) IF PRECEDED BY A LETTER

YEAR	Y	WORK WEEK	W
2001	A	27	A
2002	B	28	B
2003	C	29	C
2004	D	30	D
2005	E		
1996	F		
1997	G		
1998	H		
1999	J		
2000	K	50	X
		51	Y
		52	Z

Notes: This part marking information applies to devices produced after 02/26/2001

W = (1-26) IF PRECEDED BY LAST DIGIT OF CALENDAR YEAR



PART NUMBER CODE REFERENCE:

- A = IRLMS1902
- B = IRLMS1503
- C = IRLMS6702
- D = IRLMS5703
- E = IRLMS6802
- F = IRLMS4502
- G = IRLMS2002
- H = IRLMS6803

YEAR	Y	WORK WEEK	W
2001	1	01	A
2002	2	02	B
2003	3	03	C
2004	4	04	D
2005	5		
1996	6		
1997	7		
1998	8		
1999	9		
2000	0	24	X
		25	Y
		26	Z

W = (27-52) IF PRECEDED BY A LETTER

YEAR	Y	WORK WEEK	W
2001	A	27	A
2002	B	28	B
2003	C	29	C
2004	D	30	D
2005	E		
1996	F		
1997	G		
1998	H		
1999	J		
2000	K	50	X
		51	Y
		52	Z

This product has been designed and qualified for the consumer market.
 Qualification Standards can be found on IR's Web site.